

U.S. Department of Commerce, Patent and Trademark Office		Atty. Docket No.	Serial No.
		M-15212 US	Unassigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant(s) Chia-Shun Hsiao et al.	
		Filing Date	Group
		Herewith	Unassigned

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
WD	AA	2003/0067806	10 Apr. 2003	Tuan			
WD	AB	6,355,524	12 Mar. 2002	Tuan et al.			
WD	AC	6,541,324	1 Apr. 2003	Wang			
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents

		Document	Date	Country	Class	Subclass	Translation	
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

WD	AQ	K. Naruke et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select-Gate on Its Source Side", IEDM Technical Digest 1989, pages 603-606.
WD	AR	United States Application No.: 10/402,698 filed March 28, 2003 by Chung et al.
WD	AS	R. Mih et al., "0.18um Modular Triple Self-Aligned Embedded Split-Gate Flash Memory", 2000 Symposium on VLSI Technology, Digest of Technical Papers, pages 120-121.

Examiner John W. Hsiao Date Considered 04/26/2005

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.